

**CLAIM LISTING**

Listing of the claims is as follows:

1. (Previously Amended) An organic EL device, comprising:  
a thin film transistor (TFT) array substrate including a first insulating substrate, a TFT with a conductive interface pad connected thereto and a capacitor formed on the first insulating substrate; and  
an organic EL substrate including a second insulating substrate, a transparent electrode, an organic EL layer and a metal electrode,  
wherein the conductive interface pad is directly connected to the metal electrode.
2. (Previously Canceled)
3. (Previously Amended) The device of claim 1, wherein the organic EL substrate further includes a protection film that prevents external oxygen and moisture from permeating.
4. (Original) The device of claim 3, wherein the protection film is formed by depositing a SiNx layer and a SiO<sub>2</sub> layer at least once.
5. (Original) The device of claim 4, wherein the TFT array substrate and the organic EL substrate are sealed by a UV-curable agent.

6. (Previously Amended) An organic EL device, comprising:

a thin film transistor (TFT) array substrate including a first insulating substrate, a TFT with a conductive interface pad connected thereto, a capacitor formed on the first insulating substrate and a conductive bump pad formed on the conductive interface pad; and

an organic EL substrate including a second insulating substrate, a transparent electrode, an organic EL layer and a metal electrode,

wherein the conductive bump pad is directly connected to the metal electrode.

7. (Previously Amended) The organic EL device of claim 25, wherein the conductive bonding agent is an anisotropic conductive film (ACF).

8. (Previously Amended) The organic EL device of claim 7, wherein the anisotropic conductive film prevents external oxygen and moisture.

9. (Previously Amended) An organic EL device, comprising:

a thin film transistor (TFT) array substrate including a first insulating substrate, a TFT, a capacitor formed on the first insulating substrate, a conductive interface pad and a conductive bump pad formed on the conductive interface pad; and

an organic EL substrate including a second insulating substrate, a transparent electrode, an organic EL layer and a metal electrode, and a polymer bump,

wherein the conductive bump pad contacts a portion of the metal electrode corresponding to the polymer bump by a conductive bonding agent, and

wherein the TFT is electrically connected to the metal electrode.

10. (Original) The device of claim 9, wherein the conductive bonding agent is an anisotropic conductive film (ACF).

11. (Previously Amended) The device of claim 10, wherein the anisotropic conductive film prevents oxygen and moisture from permeating through the second insulating substrate.

12. (Original) The device of claim 1, wherein the transparent electrode, the organic EL layer and the metal electrode are sequentially stacked on the second insulating layer.

13 - 24. (Withdrawn)

25. (Previously Added and Canceled)